

PTO/SB/08A (10-01)

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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

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Sheet 1 of 2

**Complete if Known**

Application Number	08/530,661
Filing Date	September 20, 1995
First Named Inventor	Keeth et al.
Group Art Unit	2814
Examiner Name	D. Wille
Attorney Docket Number	5990US (95-0424.00/US)

**U.S. PATENT DOCUMENTS**

Examiner Initials *	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2</sup> (if known)			
D. Wille		US- 5,013,680	05/07/91	Lowrey et al.	
		US- 5,055,898	10/08/91	Beilstein, Jr. et al.	
		US- 5,107,459	04/21/92	Chu et al.	
		US- 5,396,450	03/07/95	Takashima et al.	
		US- 5,555,519	08/10/96	Takashima et al.	
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**FOREIGN PATENT DOCUMENTS**

Examiner Initials *	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)				

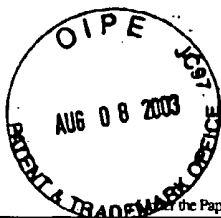
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SignatureDate  
Considered

20 Jan 04

\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

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## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 2 of 2

### Complete if Known

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Group Art Unit	2814
Examiner Name	D. Wille
Attorney Docket Number	59901US (95-0424 00/1US)

### OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
Dko		European Search Report completed 26 February 2003 for European Application No. EP 03,001,319.	
		Asakura, M., "An Experimental 256-Mb DRAM with Boosted Sense-Ground Scheme," 29(11) IEEE Journal of Solid-State Circuits 1303-09 (Nov. 1994).	
		Denboer, Anthony, "Inside Today's Leading Edge Microprocessors," Semiconductor International (Feb. 1994).	
		Hamamoto, T., et al., "NAND-Structured Trench Capacitor Cell Technologies for 256 MB DRAM and Beyond," IEICE Transactions on Electronics, Institute of Electronics Information and Comm. Eng. Tokyo, JP, Vol. E78-C, NR. 7, pp. 789-796 (July 1995).	
		Sunouchi, K., et al., "A Surrounding Gate Transistor (SGT) cell for 64/256 Mbit DRAMs," EEDM 89 23 (1989), IEEE Inc., New York NY, pp. 2.1.1-2.1.4.	
		Watanabe, S., et al., "A Novel Circuit Technology with Surrounding Gate Transistors (SGTs) for Ultra High Density DRAM's" 30(9) IEEE Journal of Solid-State Circuits 960-70 (September 1, 1995).	

Examiner Signature	<i>Douglas Wille</i>	Date Considered	20 Jan 04
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